EC6201 ELECTRONIC DEVICES L T P C
3 0 0 3

OBJECTIVES:

- To acquaint the students with the construction, theory and operation of the basic electronic devices such as PN junction diode, Bipolar and Field effect Transistors, Power control devices, LED, LCD and other Opto-electronic devices

UNIT I SEMICONDUCTOR DIODE 9

PN junction diode, Current equations, Diffusion and drift current densities, forward and reverse bias characteristics, Switching Characteristics.

UNIT II BIPOLAR JUNCTION 9

NPN -PNP -Junctions-Early effect-Current equations – Input and Output characteristics of CE, CB CC-Hybrid -π model - h-parameter model, Ebers Moll Model- Gummel Poon-model, Multi Emitter Transistor.

UNIT III FIELD EFFECT TRANSISTORS 9

JFETs – Drain and Transfer characteristics,-Current equations-Pinch off voltage and its significance-MOSFET- Characteristics- Threshold voltage -Channel length modulation, D-MOSFET, E-MOSFET-,Current equation - Equivalent circuit model and its parameters, FINFET,DUAL GATE MOSFET.

UNIT IV SPECIAL SEMICONDUCTOR DEVICES 9

Metal-Semiconductor Junction- MESFET, Schottky barrier diode-Zener diode-Varactor diode –Tunnel diode- Gallium Arsenide device, LASER diode, LDR.

UNIT V POWER DEVICES AND DISPLAY DEVICES 9

UJT, SCR, Diac, Triac, Power BJT- Power MOSFET- DMOS-VMOS. LED, LCD, Photo transistor, Opto Coupler, Solar cell, CCD.

TOTAL : 45 PERIODS

TEXT BOOKS

1. Donald A Neaman, “Semiconductor Physics and Devices”, Third Edition, Tata Mc GrawHill Inc. 2007.

REFERENCES:

1. Yang, “Fundamentals of Semiconductor devices”, McGraw Hill International Edition, 1978.
2. Robert Boylestad and Louis Nashelsky, “Electron Devices and Circuit Theory” Pearson Prentice Hall, 10th edition,July 2008.